

GS1A THRU GS1M

SMAG Plastic-Encapsulate Diodes

General Purpose Rectifier

Features

•I₀ 1A

●VRRM 50V-1000V

High surge current capability

Glass passivated chip

Polarity: Color band denotes cathode

Applications

Rectifier

Marking

• GS1X

X: From A To M



Limiting Values (Absolute Maximum Rating)

ltom.	Symbol	Unit	Canditions	GS1							
Item			Conditions	Α	В	D	G	J	K	M	
Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000	
Maximum RMS Voltage	V _{RMS}	V		35	70	140	280	420	560	700	
Average Forward Current	I _{F(AV)}	Α	60Hz Half-sine wave, Resistance load, Ta=100°C	1							
Surge(Non-repetitive)Forward Current	I _{FSM}	Α	60Hz Half-sine wave,1 cycle, Ta=25℃	30							
Junction Temperature	TJ	$^{\circ}$		-55~+150							
Storage Temperature	T _{STG}	$^{\circ}$		-55 ~ +150							

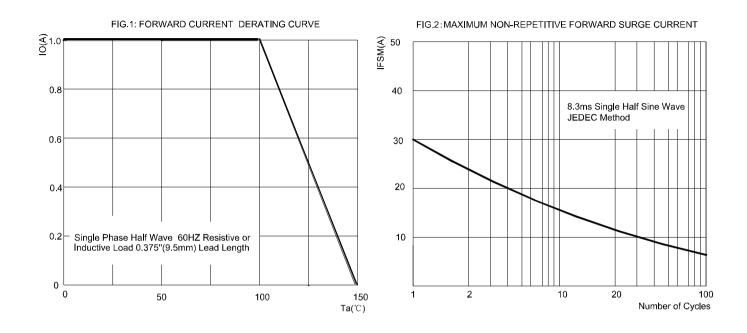
Electrical Characteristics (Ta=25℃ Unless otherwise specified)

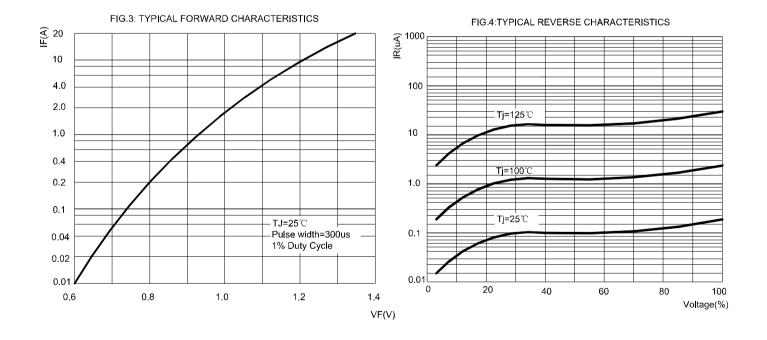
	Sumbal Unit Tast Cana		ndition	GS1								
Item	Symbol	Unit	Test Condition			В	D	G	J	K	M	
Peak Forward Voltage	$V_{\sf FM}$	V	I _{FM} =1.0A			1.0						
Peak Reverse Current	IRRM1	μΑ	\/ -\/	T _a =25℃				5				
reak Neverse Current	I _{RRM2}		V _{RM} =V _{RRM}	T _a =100℃				50)			
Thermal	$R_{\theta J-A}$	°C/W	Between junction and ambient			55						
Resistance(Typical)	R _{θJ-L}	CIVV	Between junction and lead			25						

Notes:

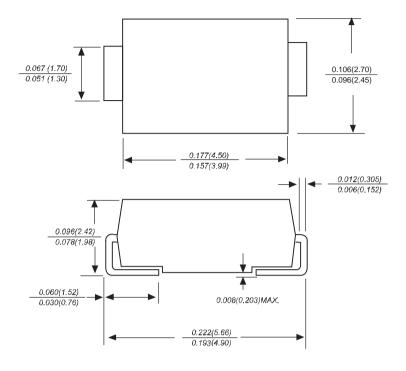
Thermal resistance from junction to ambient and from junction to lead mounted on P.C.B. with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas

Typical Characteristics



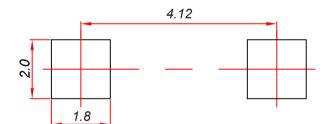


SMAG Package Outline Dimensions



Dimensions in inches and (millimeters)

SMAG Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

NOTICE

JSHD reserve the right to make modifications,enhancements, improvements, corrections or other changes without further notice to any product herein. JSHD does not assume any liability arising out of the application or use of any product described herein.

Reel Taping Specifications For Surface Mount Devices-SMAG

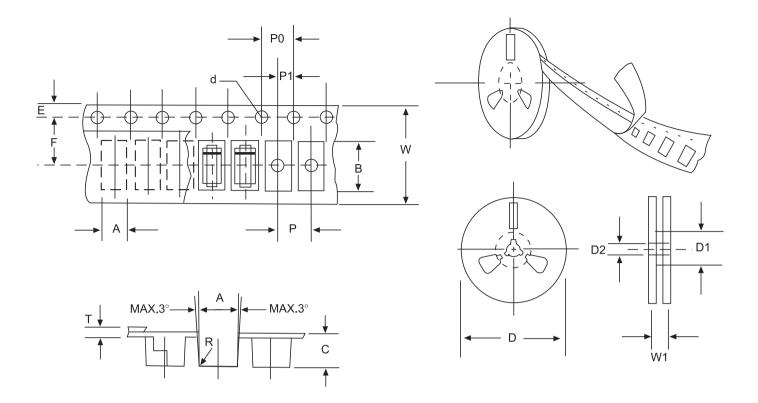


Fig:CONFIGURATION OF FLAT MELF TAPING

ITEM	SYMBOL	SMAG mm(inch)		
Carrier width	А	2.79±0.1(0.110±0.004)		
Carrier length	В	5.33±0.1(0.210±0.004)		
Carrier depth	С	2.36±0.1(0.093±0.004)		
Sprocket hole	d	1.55±0.05 (0.061±0.002)		
Reel outside diameter	D	279±2.0 (11±0.079)		
Reel inner diameter	D1	75±1.0 (2.95±0.039)		
Feed hole diameter	D2	13±0.5(0.512±0.020)		
Strocket hole position	E	1.75±0.1(0.069±0.004)		
Punch hole position	F	5.5±0.05(0.217±0.002)		
Punch hole pitch	Р	4.0±0.1(0.157±0.004)		
Sprocket hole pitch	P0	4.0±0.1(0.157±0.004)		
Embossment center	P1	2.0±0.1(0.079±0.004)		
Totall tape thickness	Т	0.28±0.02(0.011±0.0008)		
Tape width	W	12.0±0.2(0.472±0.008)		
Reel width	W1	16.8±2.0(0.661±0.079)		

NOTE:Devices are packde in accordance with EIA standard RS-481-A and specification given above.

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